PROCESS CPD48V

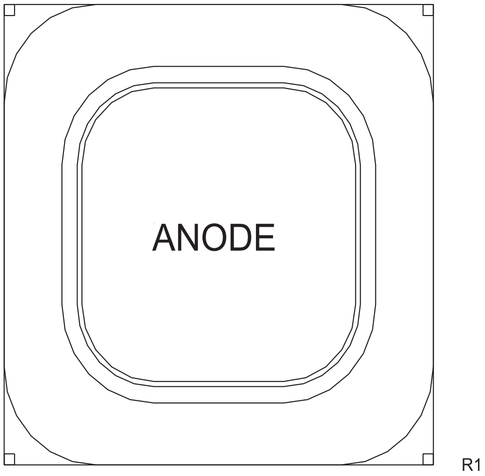
Schottky Diode

High Current Schottky Diode Chip

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	13.8 x 13.8 MILS
Die Thickness	7.1 MILS
Anode Bonding Pad Area	9.0 x 9.0 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



BACKSIDE CATHODE

GROSS DIE PER 5 INCH WAFER
89,720

PRINCIPAL DEVICE TYPES
CMPSH-3 Series
CMSSH-3 Series
CMXSH-3
CMKSH-3T

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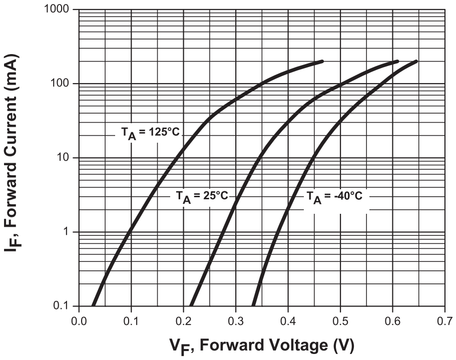
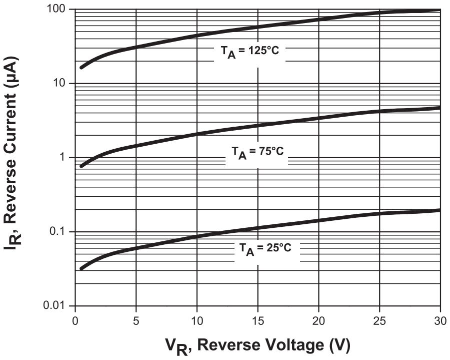
PROCESS CPD48V

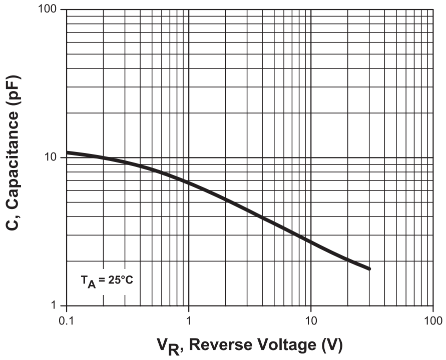
Typical Electrical Characteristics



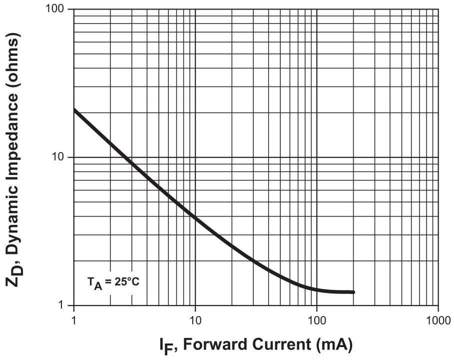
Forward Voltage



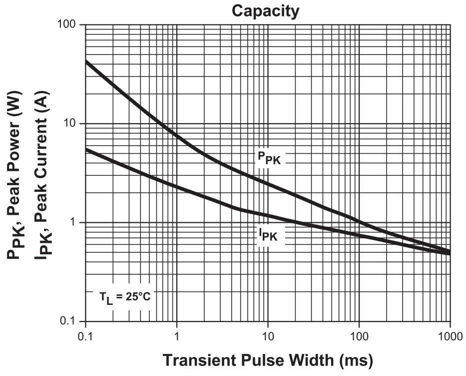
Leakage Current



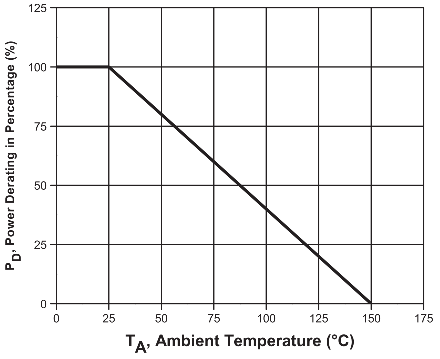
Capacitance



Forward Dynamic Impedance



Transient Peak Power and Peak Current Capacity



Normalized Power Derating

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